

DEFECT CHARACTERIZATION OF SILICON DENDRITIC
WEB RIBBONS

JET PROPULSION LABORATORY

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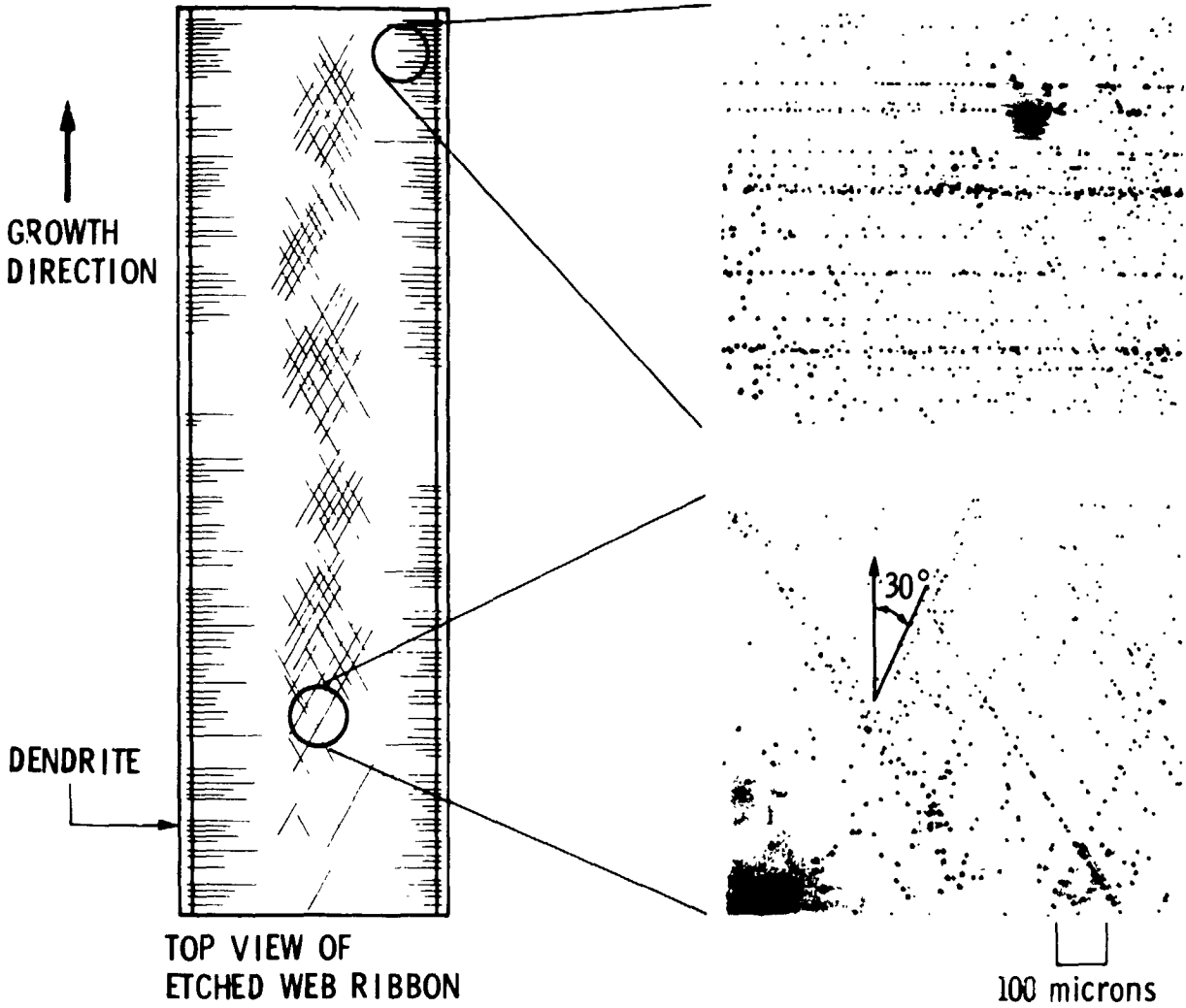
Contents

- * Etch Pit Distribution

- * Cross—Section EBIC

- * Thermal Annealing Effect on
Carrier Lifetime

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Patterns of Etch Pits on Web Ribbon Surface
Due to Dislocations

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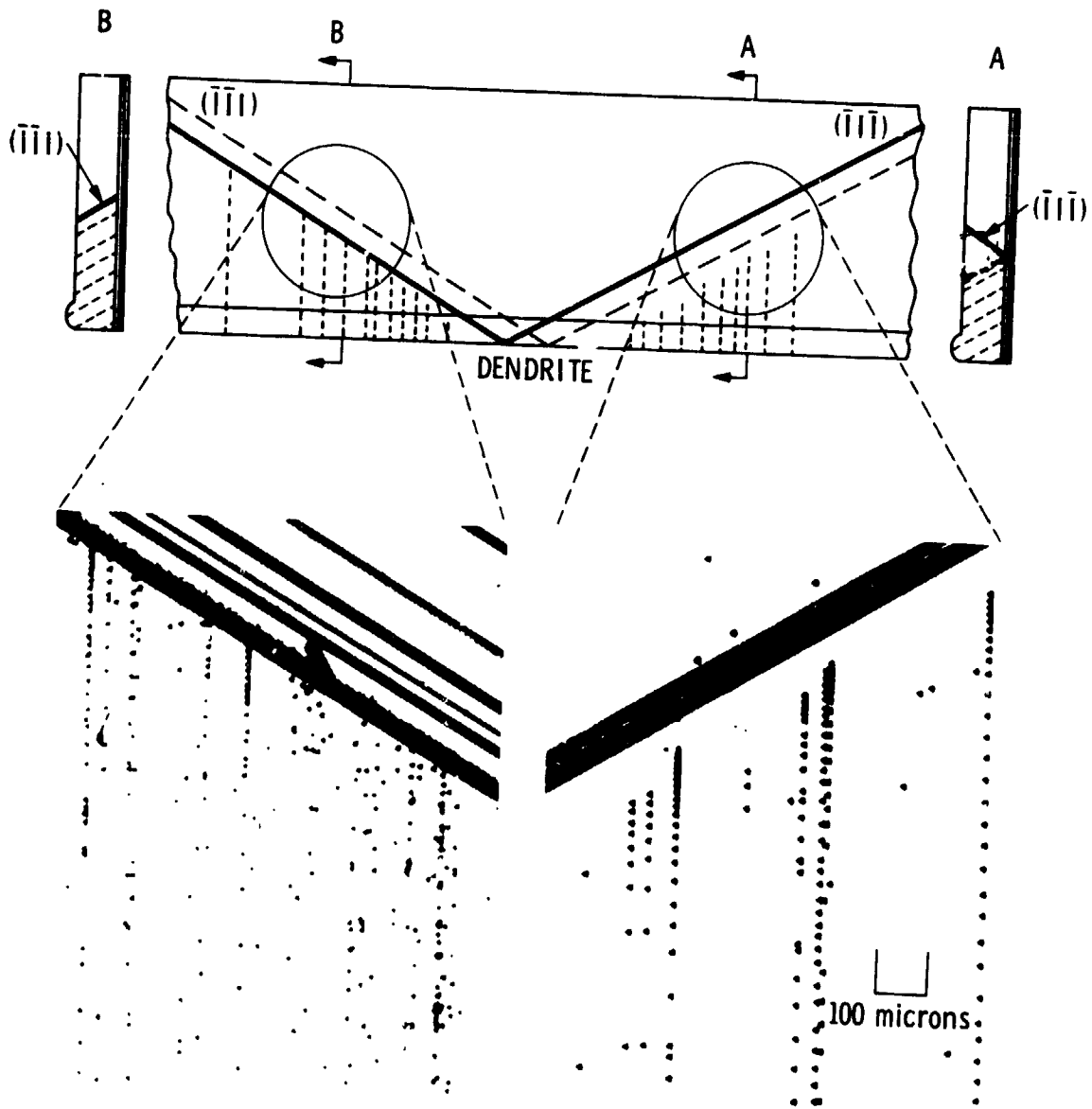


ADVANCED SILICON SHEET

Possible Movement of Three Major Slip Planes Under Stress

NATURE OF STRESS	DIRECTION WITH RESPECT TO GROWTH AXIS	INTERCEPTS ON WEB SURFACE
TENSILE	PARALLEL, σ_{xx}	✱
	PERPENDICULAR, σ_{yy}	X
SHEAR	PARALLEL, σ_{yx}	X
	PERPENDICULAR, σ_{xy}	—

ADVANCED SILICON SHEET

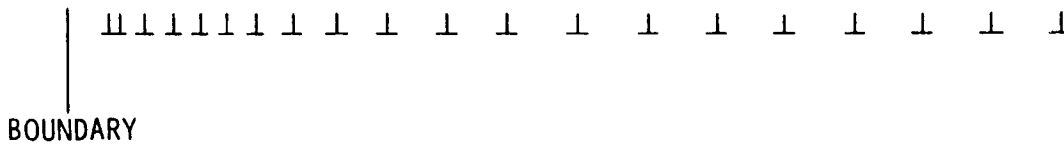
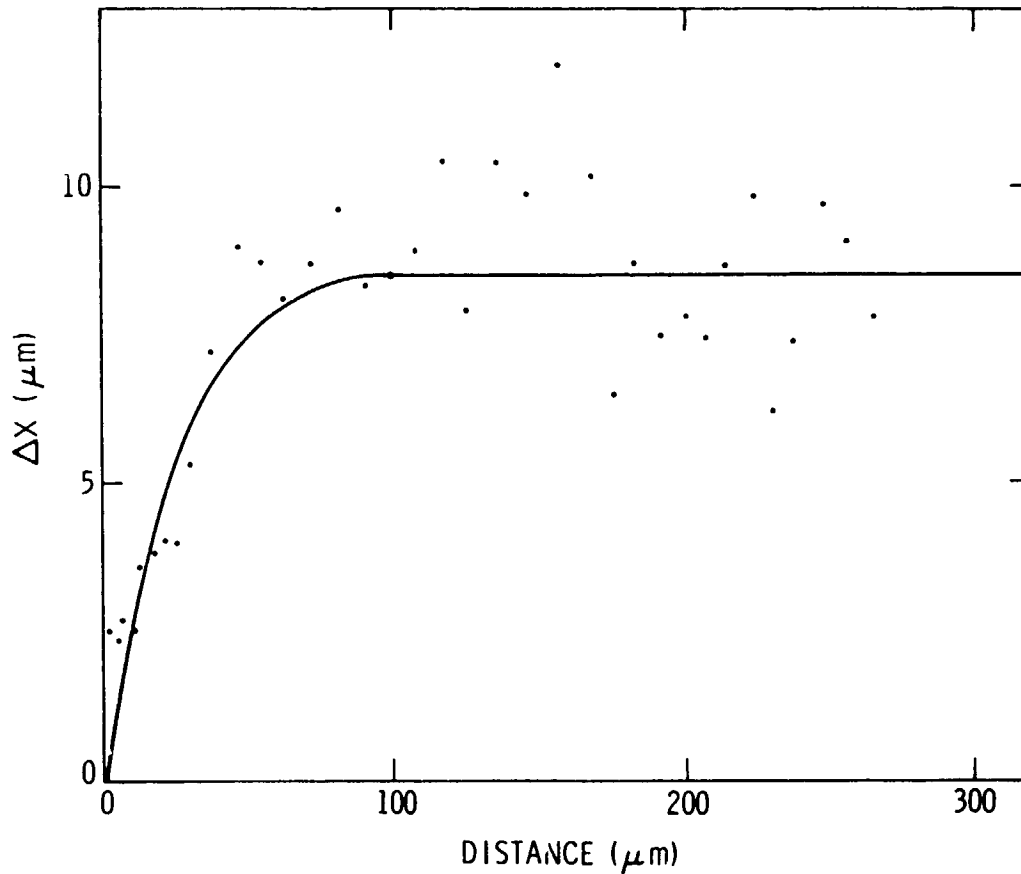


— INTERCEPTS OF $(\bar{1}\bar{1}1)$ AND $(\bar{1}\bar{1}\bar{1})$ TWIN BOUNDARIES WITH THE RIBBON SURFACE

- - - INTERCEPTS OF $(\bar{1}\bar{1}1)$ AND $(\bar{1}\bar{1}\bar{1})$ TWIN BOUNDARIES WITH THE TWIN PLANE

- - - ETCH PIT LINES DUE TO SLIP DISLOCATIONS $[101]$

— THE TWIN PLANE IN THE CENTER OF THE RIBBON PARALLEL TO THE SURFACE



TOTAL STRESS ON THE FIRST DISLOCATION DUE TO THE PRESENCE OF NEIGHBORING DISLOCATIONS ALIGNING ALONG x DIRECTION

$$\sigma_{xy}^{tot} = \frac{\mu b}{2\pi(1-\gamma)} \sum_i \frac{1}{x}$$

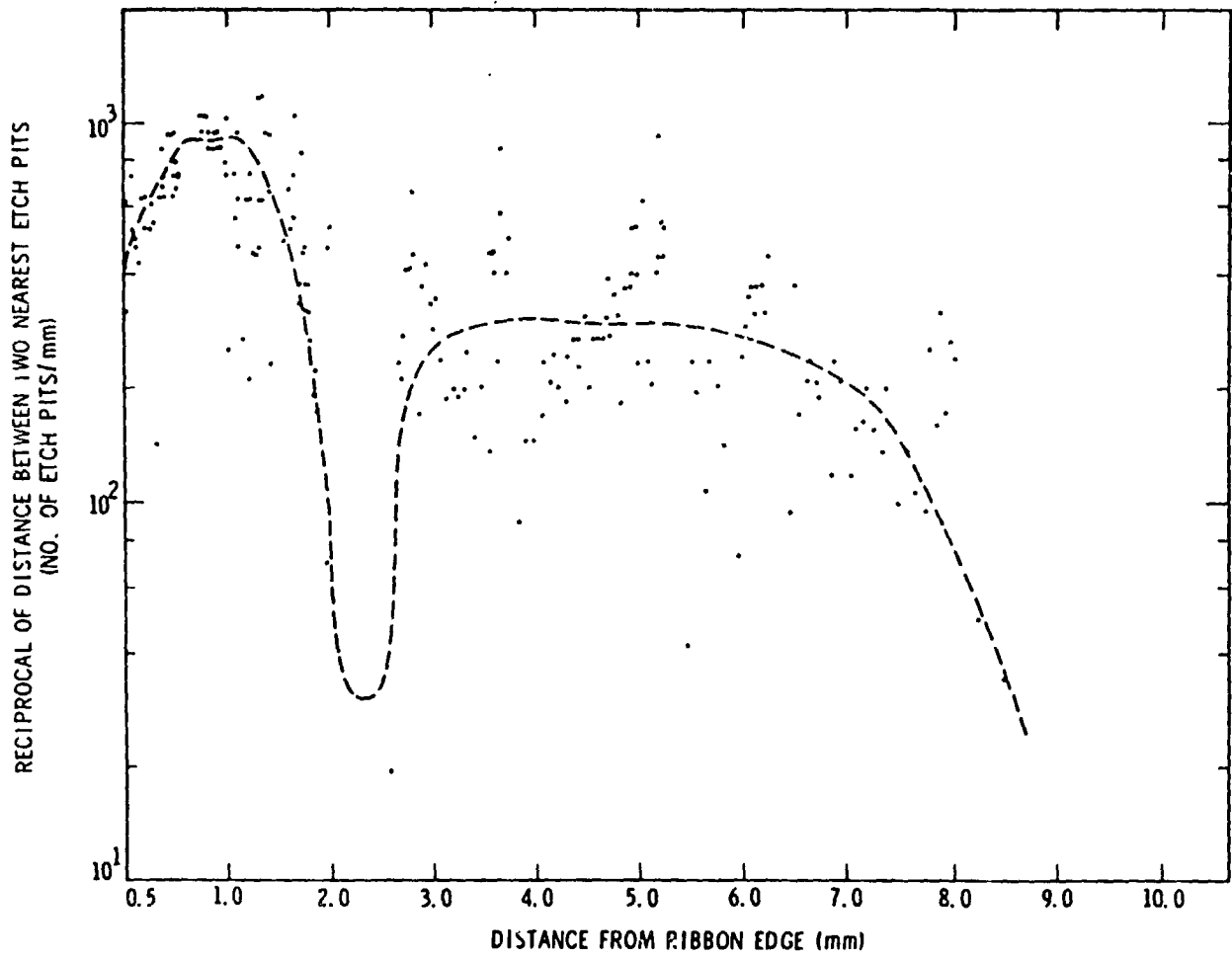
EXPERIMENTAL DATA

$$\sigma_{xy}^{tot} \text{ (AT THE PILEUP)} = 1.07 \times 10^8 \text{ dynes/cm}^2 \text{ (} 1.55 \times 10^3 \text{ PSI)}$$

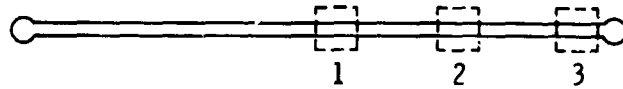
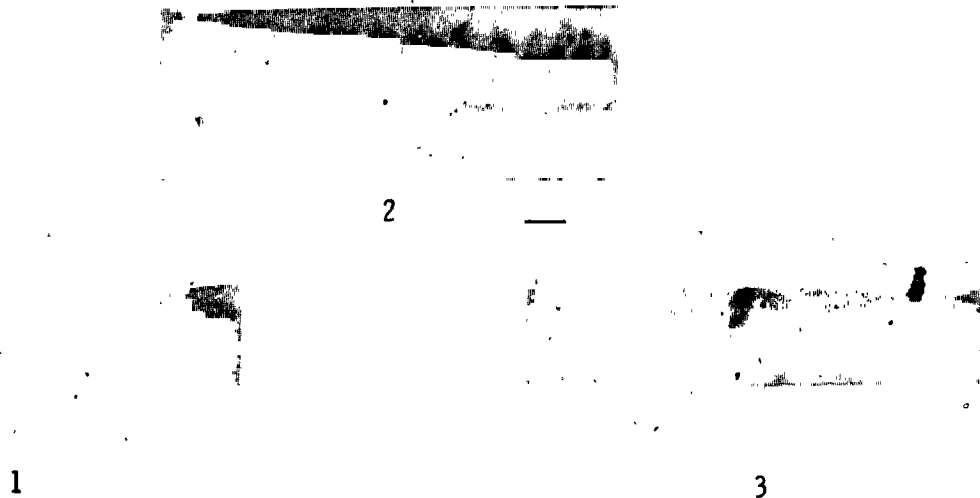
USING $\gamma = 20 \text{ PSI}$

$$\mu = \frac{\gamma}{2(1-\gamma)} = 9.57 \times 10^{11} \text{ dynes/cm}^2$$

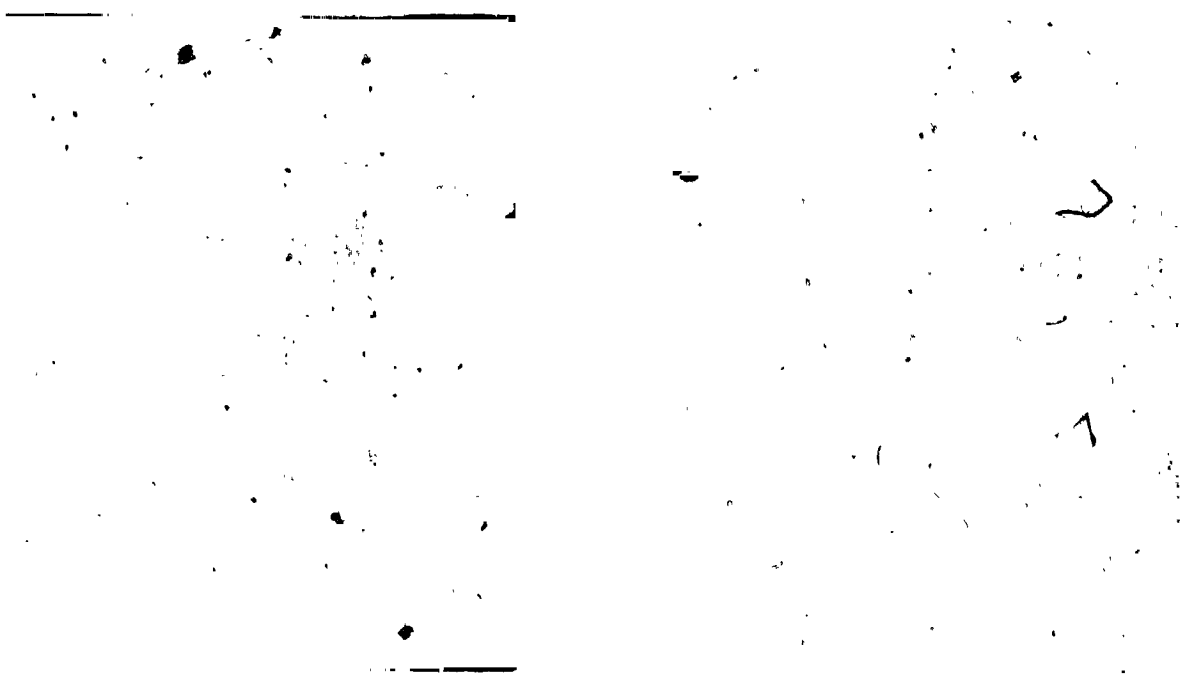
ADVANCED SILICON SHEET



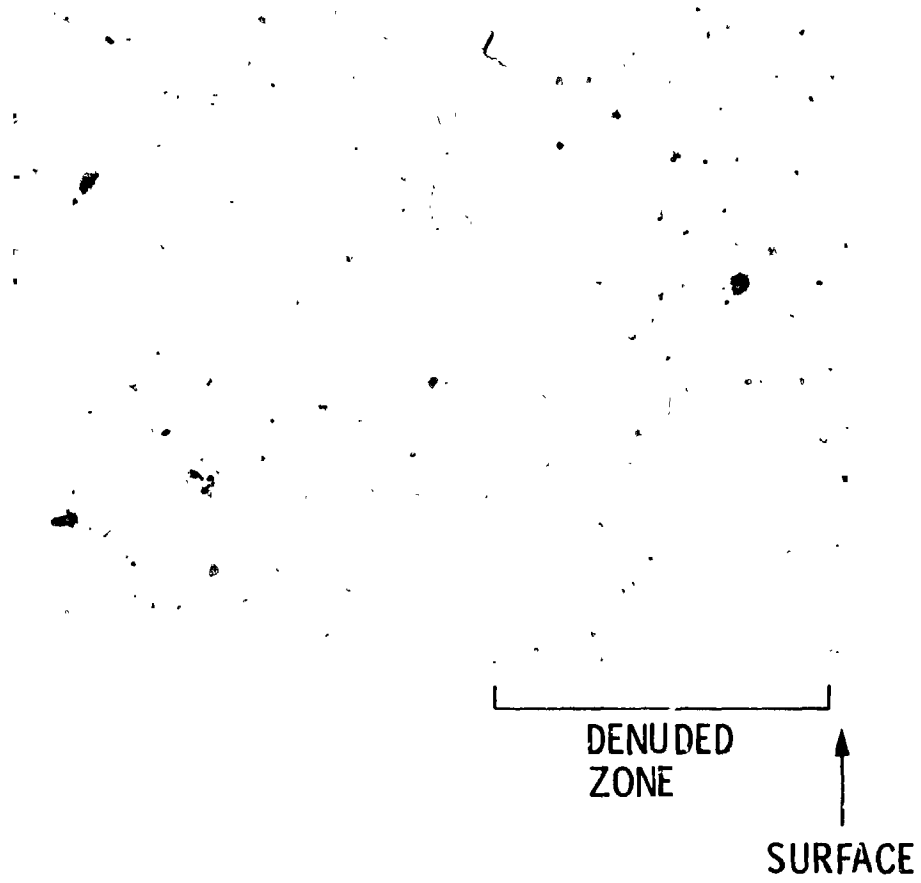
Cross-Section EBIC in As-Grown Web Ribbons (taken at room temperature)



Temperature Dependence of EBIC in Diffused Silicon Web Ribbon



SEM Picture of Etched Cross-Section of Silicon Web Ribbon



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Effect of Diffusion

